

# Computer Organization and Architecture

## Memory Unit-Introduction

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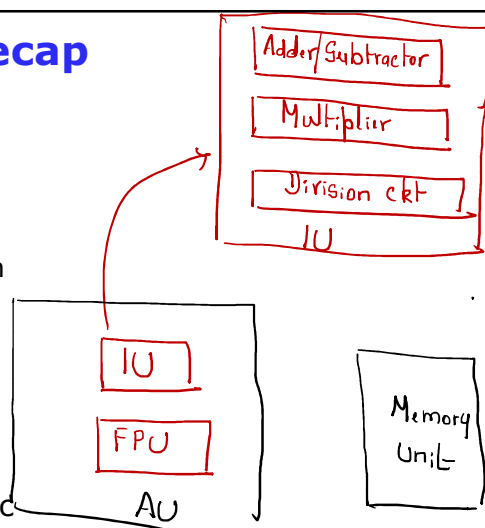


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### Recap

- Arithmetic unit design
- Integer arithmetic
  - Number representation
    - Signed
    - Unsigned
  - Adder/Subtractor
  - Multipliers
  - Division circuit
- Floating point Arithmetic
  - IEEE 754 single and double precision formats
  - Arithmetic operations



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## Computer Memory

- Program and data they operate on are held in the memory of the computer
  - Number & character operands, as well as instructions are stored in the memory of the computer

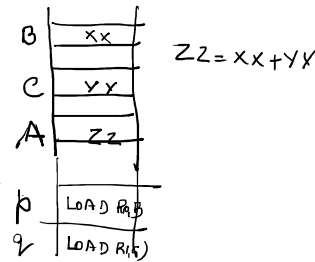
**Assignment statement:**  $A = B + C$

**LOAD** R0, B

**LOAD** R1, C

**ADD** R2, R0, R1

**STORE** A, R2



- Execution speed of programs
  - Also dependent on the speed with which instructions and data can be transferred between the processor and memory

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## Computer Memory

- Desirable to have **large memory**
  - To execute large programs
  - To handle huge amount of data
- Ideally to have memory that is **fast, large, and inexpensive**
  - Unfortunately not possible to meet this requirement
  - Increased speed and size will increase the cost too
    - **Clever solutions to address this**

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## Computer Memory

- Maximum size
  - Determined by the addressing scheme
    - 16-bit computer --- generates 16-bit addresses
      - Addressing up to  $2^{16}=64K$  memory locations

- Modern computers are byte addressable

1 bit  $\rightarrow$  cell

1 Byte

1 word  $\rightarrow$  Collection of bits  
Bytes

Word length = 32 bit

32 bit Add

Higher order (Word) 30 bits  
Lower order 2 bits  
 $\downarrow$   
byte

- Memory is designed to store and retrieve data in word-length quantities
  - Word: number of bits actually stored or retrieved in one memory access



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## Byte Addressable Memory

Word Address

Byte Address

0	3	2	1	0
1	7	6	5	4
2	11	10	9	8
⋮				
$2^{k/4}-1$	$2^k-4$	$2^k-3$	$2^k-2$	$2^k-1$

Little Endian

Example: Intel Processors

Word Address

Byte Address

0	0	1	2	3
1	4	5	6	7
2	8	9	10	11
⋮				
$2^{k/4}-1$	$2^k-1$	$2^k-2$	$2^k-3$	$2^k-4$

Big Endian

Motorola Processors

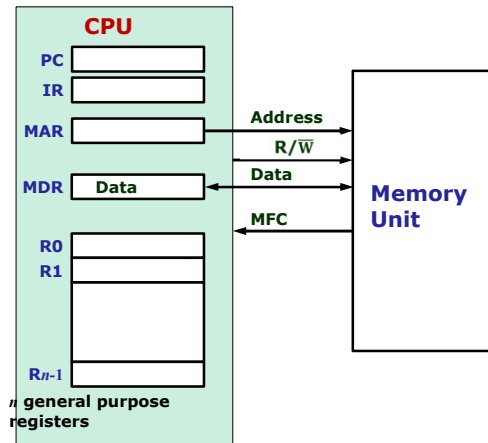
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## Memory Read and Write Operation

### • Read

- Processor loads the address of memory location into MAR
- Set the  $R/\bar{W}$  line to 1
- Memory responds by placing the data from address location onto data line
- Confirm the action by asserting MFC (memory function complete) signal
- Upon receiving MFC signal, processor loads the data on data line into MDR



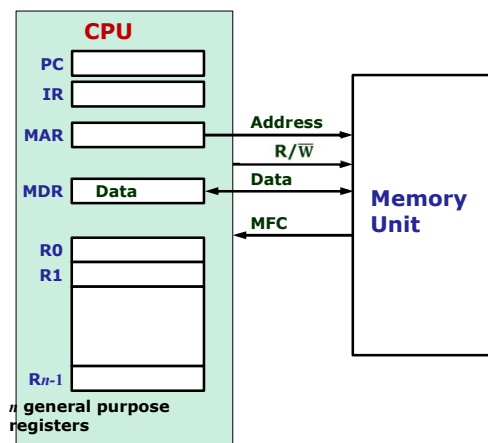
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## Memory Read and Write Operation

### • Write

- Processor loads the address of memory location into MAR
- Processor loads data into MDR
- Set the  $R/\bar{W}$  line to 0 to indicate write operation
- Processor places the data in MDR onto data line
- Data on data line is written into memory location
- Memory confirms the action by asserting MFC signal



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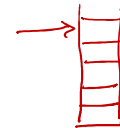
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## Computer Memory

- CPU executes the instructions for which the instructions and operands have to come from memory unit
- Operations which involve memory:
  - **Instruction fetch**
    - Memory read
  - **Memory operand fetch and store**
    - Memory read
    - Memory write
- Instructions involving memory access:
  - LOAD and STORE instructions
- Block transfer
  - If read or write operations involve consecutive address locations in the main memory
  - Only address sent is the starting address

```
LOAD R0, B }
LOAD R1, C }
ADD R2, R1, R0
STORE A, R2 }
```

```
ADDMM A, B, C
```



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## Memory Performance Parameters

- **Access Time:**
  - Time interval between initiation of one operation and completion of that operation
  - **Example:** Time between assertion of Read signal and MFC signal
- **Memory Cycle Time:**
  - Minimum time delay between the initiation of two successive memory operations
  - Time delay between start of a read/write operation to start of next memory operation
- Memory cycle time is usually slightly larger than access time

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## Memory Latency and Memory Organization

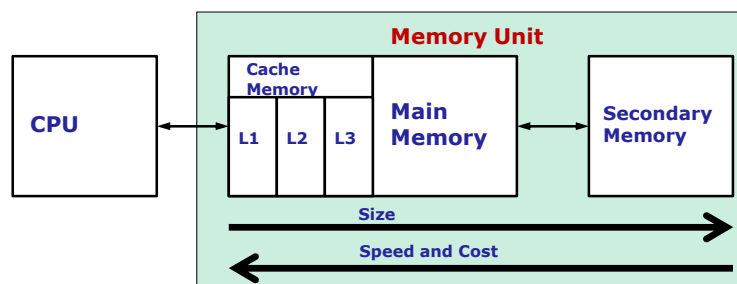
- **Latency**: Time to access the first of the sequence of memory words
- What is involved in determining the latency of the memory operation?
  - Processor issues the logical address to memory unit
  - The logical address need to be converted into physical address
- Memory unit is called random access memory (RAM)
  - Any location can be accessed for read/write operation independent of the location's address
- Memory unit is organised in **hierarchical** manner



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## Memory Hierarchy



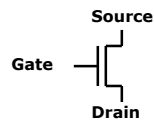
- Processor processes instructions and data faster than it can be fetched from memory unit
- **Memory access time** is the bottleneck
- One way to reduce **memory access time** is to use faster memory
  - A small and faster memory bridge the gap between processor and main memory
- **Virtual memory**

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## Semiconductor Memories

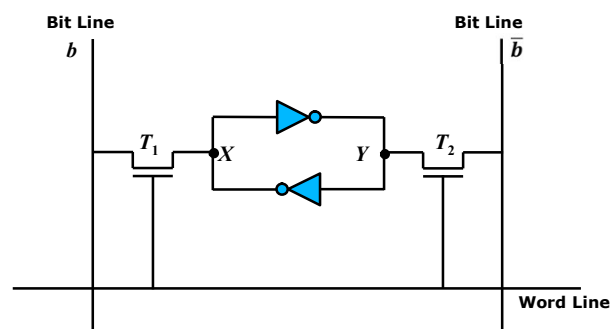
- Two basic ways of designing memory *1 bit → Memory cell*
  - Static RAM (SRAM)
  - Dynamic RAM (DRAM)
- Static RAM:**
  - Built using metal-oxide semiconductor (MOS) transistors
  - MOS transistors acts as switch
    - +5 v (when Gate input is 1): Transistor conducts: ON state
    - 0 v (when Gate input is 0): Transistor does not conducts: OFF state



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## Static RAM Cell

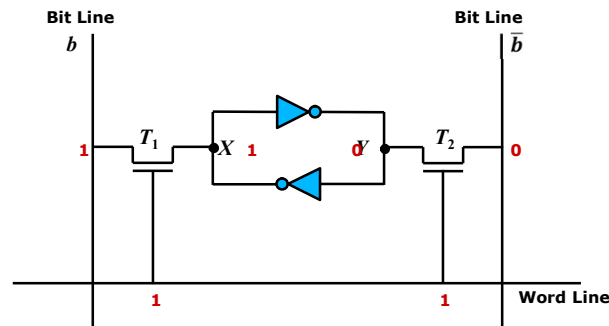


- Two inverters are cross connected to form latch
- Inverters are connected to 2 transistors which act as switches
- Switches are opened or closed under the control of word line
- This circuit retain the state (bit) as long as power is applied (Static Memory)

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## Static RAM Cell - Read

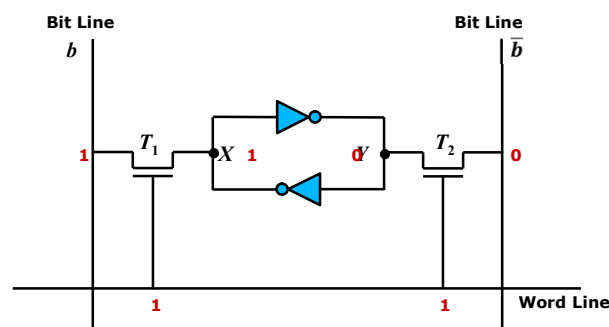


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## Static RAM Cell - Write



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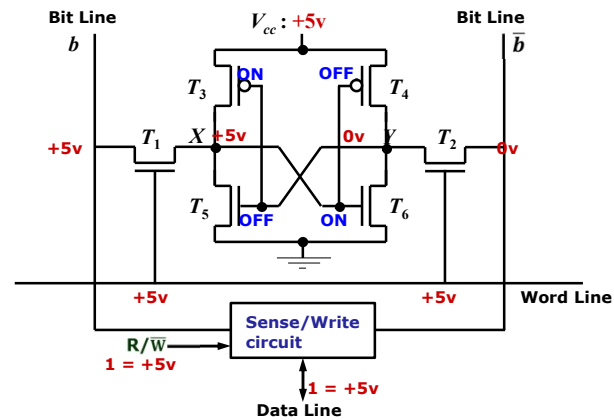
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## CMOS Static RAM Cell - Read

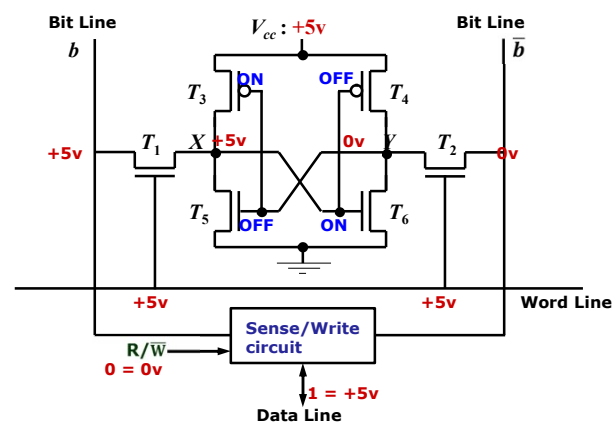


- This circuit retain the state (bit) as long as power is applied (Static Memory)
- Continuous power is needed for a cell to retain the state

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## CMOS Static RAM Cell - Write

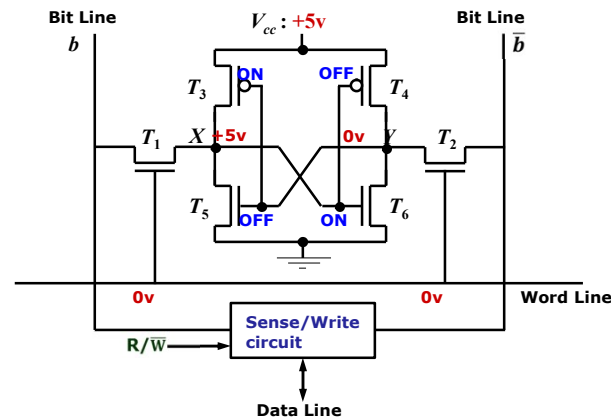


- This circuit retain the state (bit) as long as power is applied (Static Memory)
- Continuous power is needed for a cell to retain the state

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## CMOS Static RAM Cell



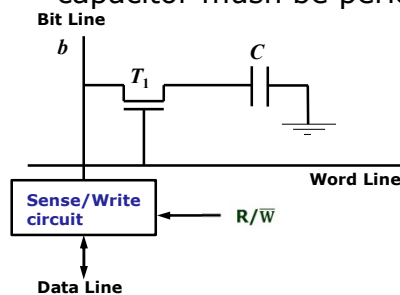
- Volatile
- Low power consumption-current flows in the cell only when the cell is accessed
- Access time is less i.e. faster memory
- Uses 6 transistors: Costly
- Used in applications where speed is critical concern: [Cache](#)

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## Dynamic RAM (DRAM) Cell

- Less expensive and simpler cell
- Information is stored in the form of a charge on a capacitor (C)
  - Charge in capacitor is stored only for short time
    - Tens of a millisecond
  - However, a cell is required to store information for a much longer time
- To retain information for longer time, content of capacitor must be periodically refreshed



- Low speed as refresh needed
- Only 1 transistor is used
- Used to build [main memory](#)

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## Reference

- Carl Hamacher, Zvonko Vranesic and Safwat Zaky, "**Computer Organization**", 5<sup>th</sup> Edition, Tata McGraw Hill, 2002

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## Thank You

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